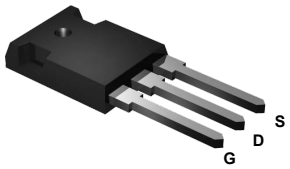
GOOD-ARK SEMICONDUCTOR

GSFA20106AU

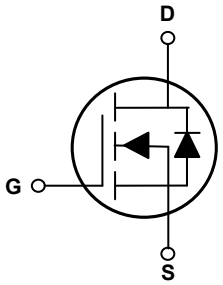
200V N-Channel MOSFET

Main Product Characteristics

BV_{DSS}	200V
$R_{DS(ON)}$	10.7mΩ (Max.)
I_D	106A



TO-247



Schematic Diagram

Features and Benefits

- Advanced MOSFET process technology
- Ideal for high efficiency switched mode power supplies
- Low on-resistance with low gate charge
- Fast switching and reverse body recovery
- AEC-Q101 qualified

Description

The GSFA20106AU utilizes the latest techniques to achieve high cell density and low on-resistance. These features make this device extremely efficient and reliable for use in high efficiency switch mode power supplies and a wide variety of other applications.

Absolute Maximum Ratings (T_J=25°C unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	200	V
Gate-to-Source Voltage	V_{GS}	±20	V
Continuous Drain Current, @ Steady-State (T_C=25°C)	I_D	106	A
Continuous Drain Current, @ Steady-State (T_C=100°C)		76	A
Pulsed Drain Current (T_C=25°C)[1]	I_{DM}	424	A
Power Dissipation (T_C=25°C)[2]	P_D	340	W
Single Pulse Avalanche Energy	E_{AS}	600	mJ
Single Pulse Avalanche Current	I_{AS}	49	A
Thermal Resistance, Junction-to-Ambient (PCB Mounted, Steady-State)	$R_{\theta JA}$	50	°C/W
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	0.44	°C/W
Operating Junction and Storage Temperature Range	T_J/T_{STG}	-55 to +175	°C
Soldering Temperature (SMD)	T_{sold}	260	°C

Electrical Characteristics (T_J=25°C unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
On / Off Characteristics						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS}=0V, I_D=250uA	200	-	-	V
Drain-Source Leakage Current	I_{DSS}	V_{DS}=200V, V_{GS}=0V, T_J=25°C	-	-	1	μA
		V_{DS}=200V, V_{GS}=0V, T_J=125°C	-	10	-	μA
Gate-Source Forward Leakage	I_{GSS}	V_{GS}=±20V, V_{DS}=0V	-	-	±100	nA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	V_{GS}=10V, I_D=88A	-	9.4	10.7	mΩ
Gate Threshold Voltage	$V_{GS(th)}$	V_{GS}=V_{DS}, I_D=250uA	2.0	-	4.0	V
Dynamic and Switching Characteristics						
Total Gate Charge[3,4]	Q_g	V_{DD}=100V, I_D=44A, V_{GS}=10V	-	64	-	nC
Gate-Source Charge[3,4]	Q_{gs}		-	28	-	
Gate-Drain ("Miller") Charge[3,4]	Q_{gd}		-	7.9	-	
Gate to Plateau[3,4]	$V_{plateau}$		-	5.3	-	V
Turn-On Delay Time[3,4]	$t_{d(on)}$	V_{DD}=100V, R_G=1.6Ω, V_{GS}=10V, I_D=44A	-	22	-	nS
Rise Time[3,4]	t_r		-	40	-	
Turn-Off Delay Time[3,4]	$t_{d(off)}$		-	66	-	
Fall Time[3,4]	t_f		-	18	-	
Input Capacitance	C_{lss}	V_{DS}=100V, V_{GS}=0V, F=1MHz	-	4720	-	pF
Output Capacitance	C_{oss}		-	430	-	
Reverse Transfer Capacitance	C_{rss}		-	11	-	
Gate Resistance	R_g	F=1MHz	-	4.9	-	Ω
Drain-Source Diode Characteristics and Maximum Ratings						
Continuous Source Current (Body Diode)	I_S	T_C=25°C, MOSFET symbol showing the integral reverse p-n junction diode.	-	-	106	A
Diode Pulse Current	$I_{S.pulse}$		-	-	424	A
Diode Forward Voltage	V_{SD}	V_{GS}=0V, I_S=88A	-	-	1.4	V
Reverse Recovery Time[3]	t_{rr}	V_{GS}=0V, I_S=44A, di_F/dt=100A/μs	-	130	-	nS
Reverse Recovery Charge[3]	Q_{rr}		-	0.7	-	μC

Note:

1. Pulse time of 5us.
2. The dissipated power value will change with the temperature. When it is greater than 25°C, the dissipated power will decrease by 2.5W/°C for every 1 degree of temperature rise.
3. Pulse test: Pulse width ≤ 300us, duty cycle ≤ 2%.
4. Essentially independent of operating temperature.

Typical Electrical and Thermal Characteristic Curves

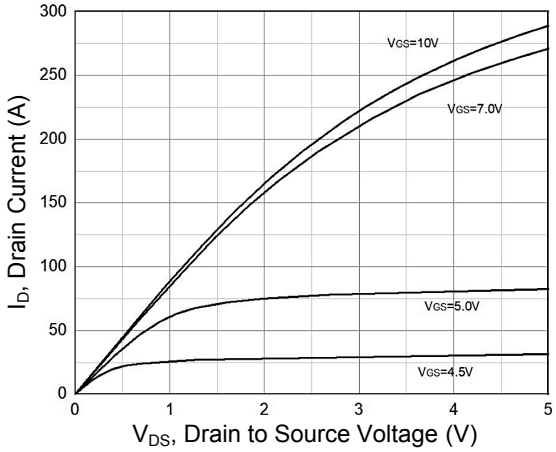


Figure 1. Typical Output Characteristics

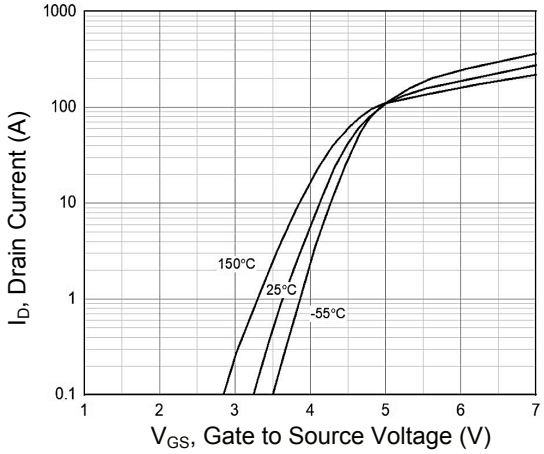


Figure 2. Transfer Characteristics

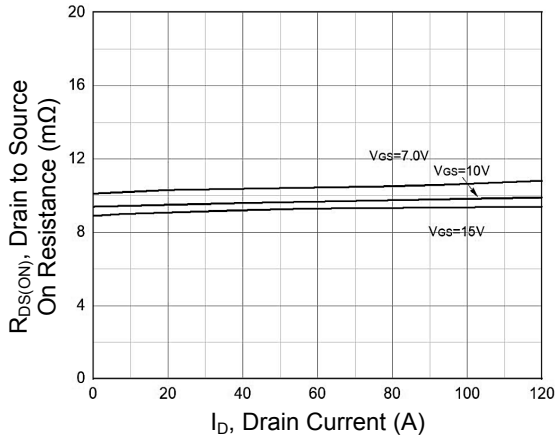


Figure 3. $R_{DS(ON)}$ vs. Drain Current

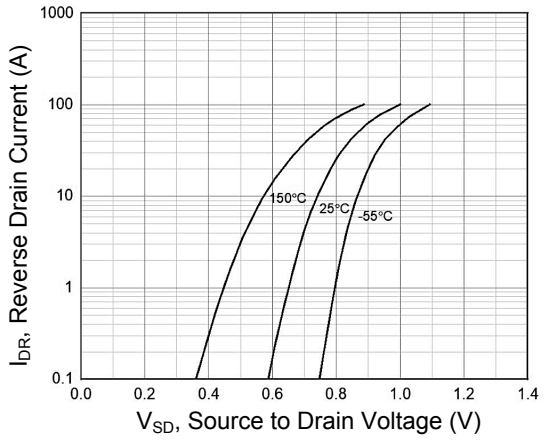


Figure 4. Body Diode Characteristic

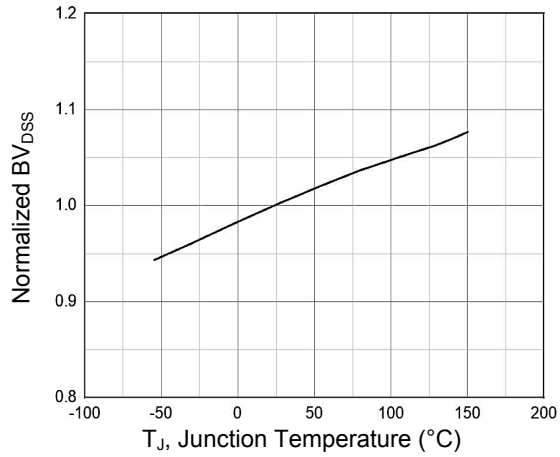


Figure 5. Normalized BV_{DSS} vs. T_J

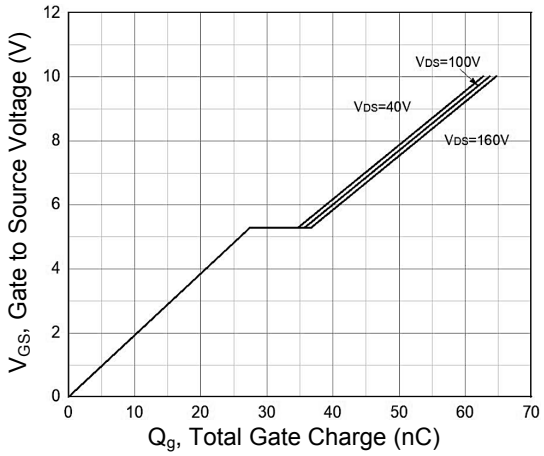


Figure 6. Gate Charge

Typical Electrical and Thermal Characteristic Curves

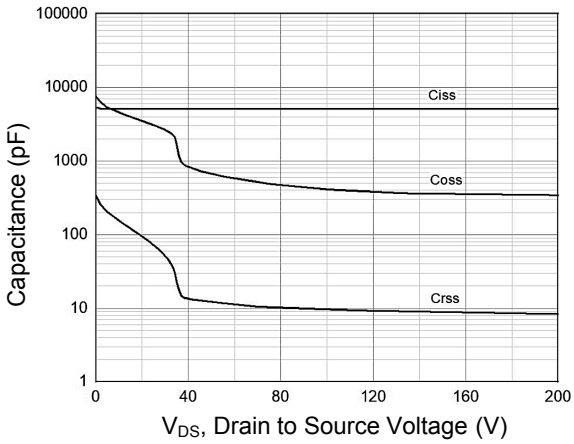


Figure 7. Capacitance Characteristic

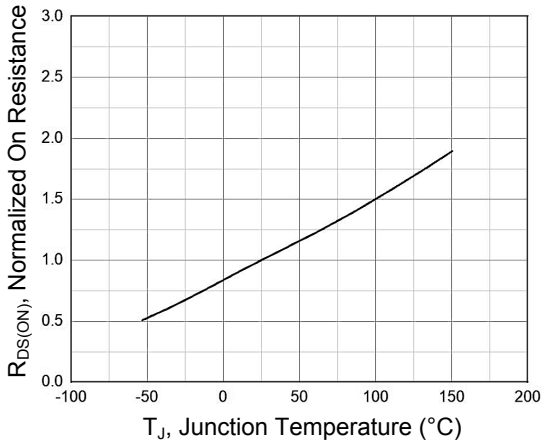


Figure 8. Normalized $R_{DS(ON)}$ vs. T_J

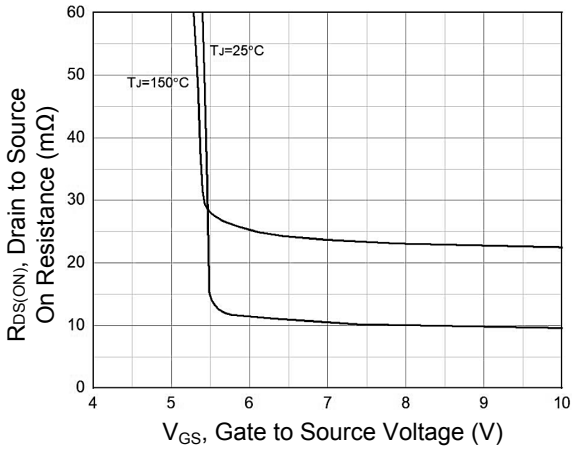


Figure 9. $R_{DS(ON)}$ vs. V_{GS}

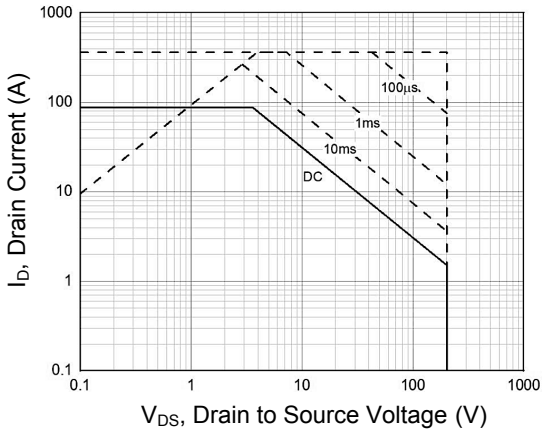


Figure 10. Safe Operation Area

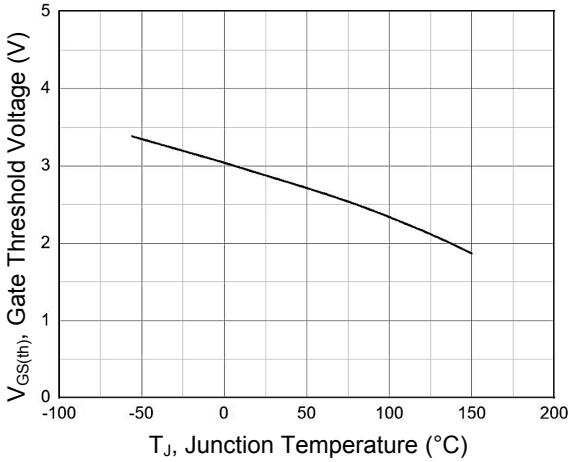


Figure 11. Gate Threshold Voltage vs. T_J

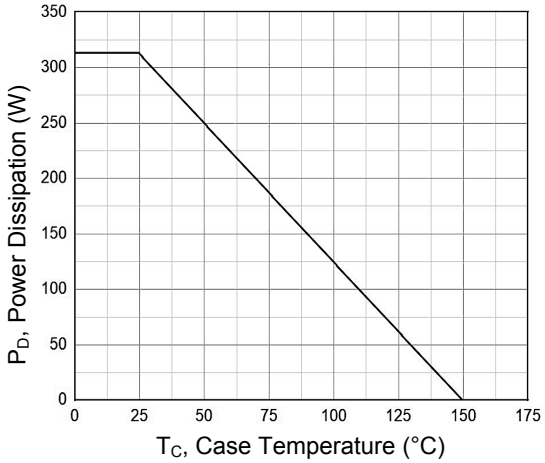
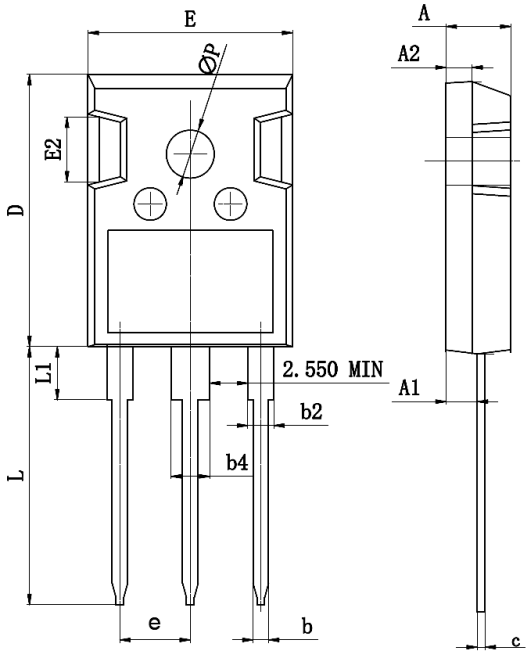


Figure 12. Power Dissipation vs. T_C

Package Outline Dimensions (TO-247)



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	4.75	5.20	0.187	0.205
A1	2.21	2.65	0.087	0.104
A2	1.85	2.15	0.073	0.085
b	1.00	1.36	0.039	0.054
b2	1.80	2.25	0.071	0.089
b4	2.91	3.25	0.115	0.128
c	0.51	0.75	0.020	0.030
D	20.80	21.30	0.819	0.839
E	15.50	16.10	0.610	0.634
E2	4.40	5.20	0.173	0.205
e	5.44 BSC		0.214 BSC	
L	19.72	20.22	0.776	0.796
L1	-	4.30	-	0.169
P	3.40	3.80	0.134	0.150

Order Information

Device	Package	Marking	Packaging	SPQ
GSFA20106AU	TO-247	A10020	Tube	30 Pcs / Tube